

MULTILAYER REFLECTIVE EXTREME  
ULTRAVIOLET LITHOGRAPHY MASK BLANKS

Abstract of the Disclosure

An extreme ultraviolet lithography mask may be formed of a multilayered stack covered by a spacer layer, such as silicon or boron carbide, in turn covered by a thin layer  
5 to prevent inter-diffusion, and finally covered by a capping layer of ruthenium. By optimizing the spacer layer thickness based on the capping layer, the optical properties may be improved.